

Features

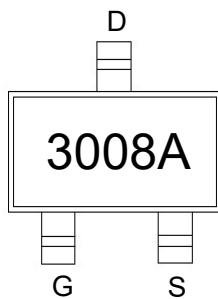
- High density cell design for ultra low $R_{DS(ON)}$
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Product Summary

V_{DS}	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
30V	15mΩ@10V	8A
	20mΩ@4.5V	

Application

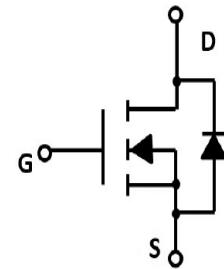
- Power switching application



3008A: Device code



SOT-23-3L top view



Schematic diagram



Halogen-Free

Marking and pin assignment

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit	
Common Ratings (TC=25°C Unless Otherwise Noted)				
V_{DS}	Drain-Source Breakdown Voltage	30	V	
V_{GS}	Gate-Source Voltage	± 20	V	
T_J	Maximum Junction Temperature	150	°C	
T_{STG}	Storage Temperature Range	-50 to 155	°C	
I_S	Diode Continuous Forward Current	8	A	
Mounted on Large Heat Sink				
I_{DM}	Pulse Drain Current Tested	Tc=25°C	32	A
I_D	Continuous Drain Current	Tc=25°C	8	A
P_D	Maximum Power Dissipation	Tc=25°C	1.1	W
$R_{θJA}$	Thermal Resistance Junction-Ambient		135 °C/W	

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLSK3008A	SOT-23-3L	3008A	3,000	45,000	180,000	7" reel

Electrical Characteristics (TJ=25°C unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V	--	--	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =6A	--	10	15	mΩ
		V _{GS} =4.5V, I _D =4A	--	15	20	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
CISS	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	--	1055	--	pF
COSS	Output Capacitance		--	180	--	pF
CRSS	Reverse Transfer Capacitance		--	130	--	pF
Switching Characteristics						
Qg	Total Gate Charge	V _{DS} =15V, I _D =6A, V _{GS} =10V	--	25	--	nC
Qgs	Gate Source Charge		--	3.5	--	nC
Qgd	Gate Drain Charge		--	6	--	nC
td(on)	Turn-on Delay Time	V _{DS} =15V, R _L =1.8Ω, V _{GS} =10V, R _G =3Ω	--	5	--	nS
tr	Turn-on Rise Time		--	12	--	nS
td(off)	Turn-Off Delay Time		--	19	--	nS
tf	Turn-Off Fall Time		--	6	--	nS
Source- Drain Diode Characteristics						
VSD	Forward on voltage	T _J =25°C, I _S =8A	--	--	1.2	V

Typical Operating Characteristics

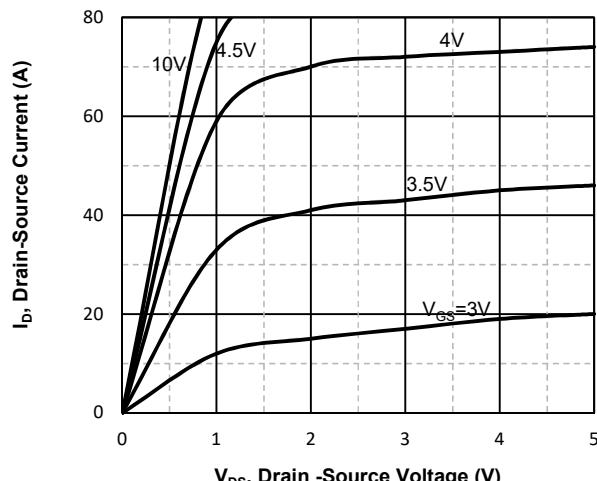


Fig1. Typical Output Characteristics

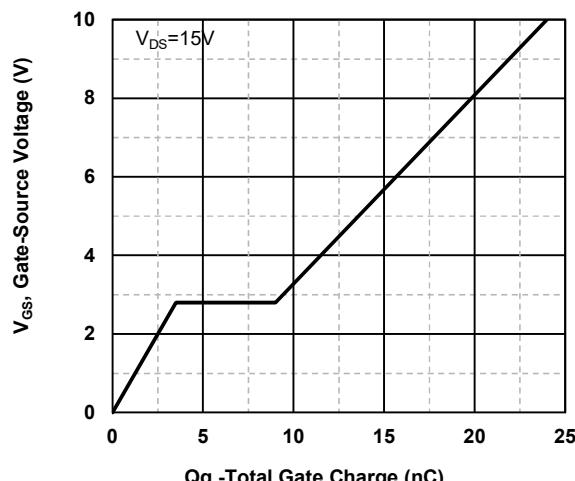


Fig2. Typical Gate Charge Vs.Gate-Source Voltage

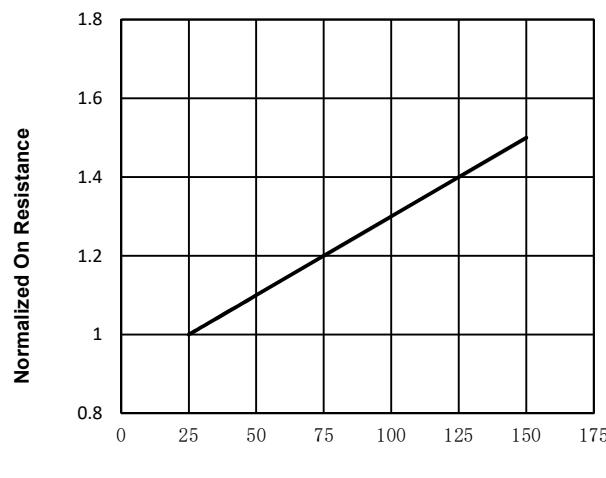


Fig3. Normalized On-Resistance Vs. Temperature

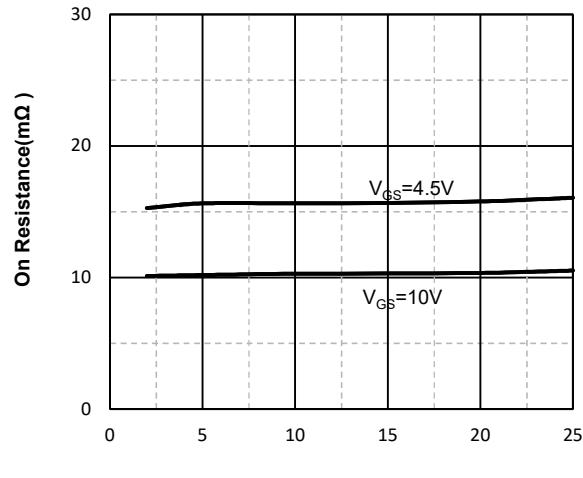


Fig4. On-Resistance Vs. Drain-Source Current

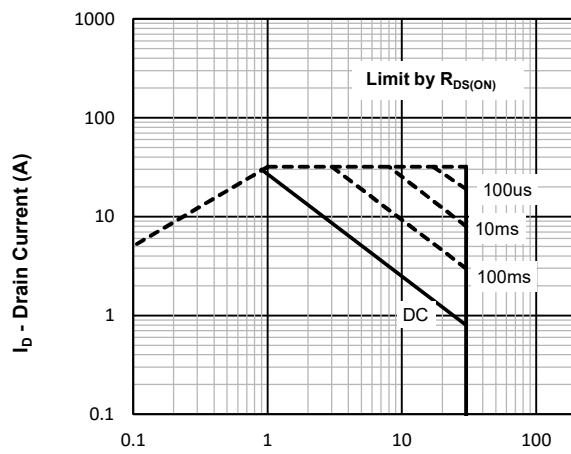


Fig5. Maximum Safe Operating Area

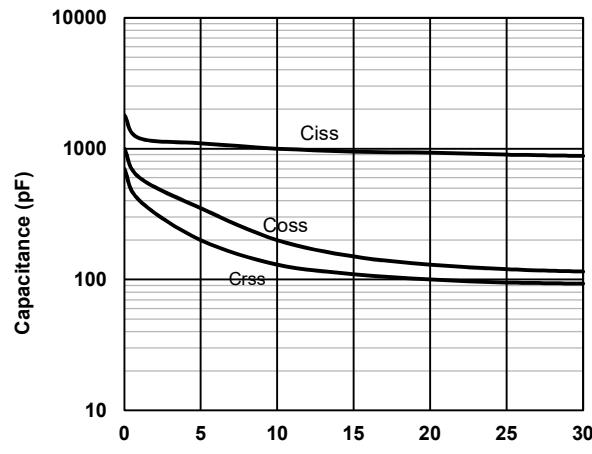
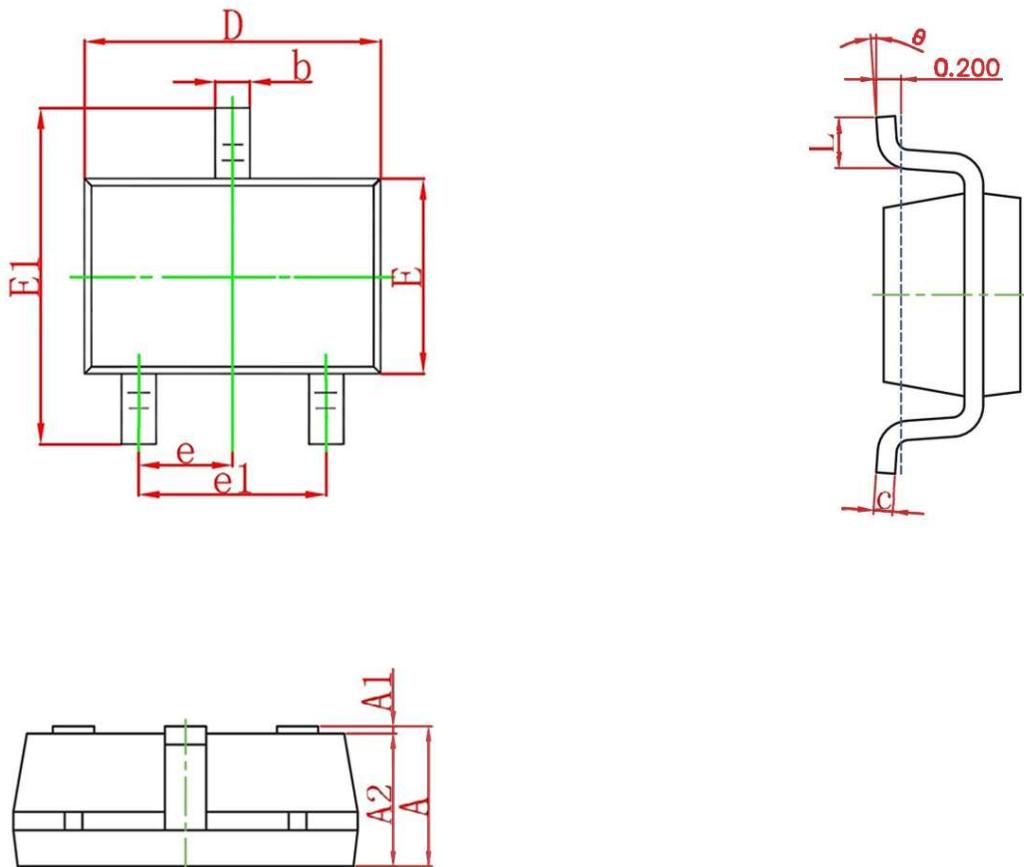


Fig6 Typical Capacitance Vs.Drain-Source

SOT-23-3L Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.042	0.050
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.042	0.046
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.112	0.120
E	1.500	1.700	0.060	0.068
E1	2.650	2.950	0.106	0.118
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°